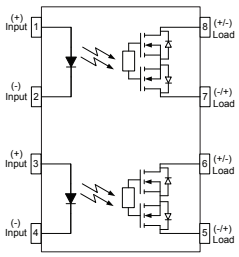
Parameter	Symbol	Rating	Units
Load Voltage	V_L	400	V
Load Current	I_L	0.15	A
On-Resistance	R_{on}	14	Ω
I/O Breakdown Voltage	V/IO	5000	Vrms

E534710

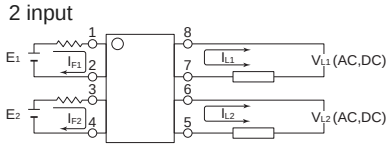
SMD-8

DIP-8

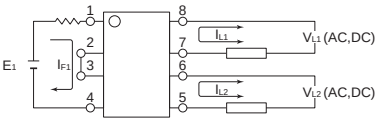


1,3. LED Anode
2,4. LED Cathode
5,6. Drain (MOS FET)
7,8. Drain (MOS FET)

(1) 2 input



(2) 1 input



APSEMI PhotoRelays

APSEMI Photorelays are the most reliable, technically advanced logic-to-power interface devices. Their basic function is to take a low current signal from a microprocessor to control the switching of both AC and DC loads, while providing an isolation barrier between logic and power.
While this function is common to all relays, Photorelays provide distinct advantages over their mechanical counterparts including:

- Long life (No limit on mechanical and electrical
- lifetime)Bounce-free switching
- Higher speed and high frequency switching
- Higher sensitivity (less power consumption)
- Immunity to EMI or RFI
- No have voltaic arc, bounce, and noise More
- resistant to vibration and impact AC or DC load
- switching
- Small package size

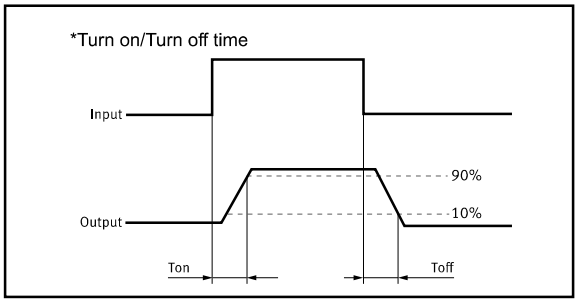
Applications

These advantages make APSEI Photorelays the ideal choice for:

- Telecom/Datacom switching
- Multiplexers
- Meter reading systems
- Data acquisition
- Medical equipment
- Battery monitoring
- I/O Sub-Systems
- Robotics
- Aerospace
- Home/Safety security systems
- Process Control
- Energy Management
- Reed Relay EMR Replacement
- Programmable Controllers

TPYES

Category	Output Rating		Package	Part No.	Packing Quantity
	Load Voltage	Load Current			
AC/DC	400V	150mA	DIP-8	APW214E	50pcs /tube
			SMD-8	APW214EH	1000pcs /reel



Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Value	Units	Note
Input	Continuous LED Current	I_F	50	mA	
	Peak LED Current	I_{FP}	1000	mA	f=100Hz, duty=1%
	LED Reverse Voltage	V_R	5	V	
	Input Power Dissipation	P_{In}	75	mW	
Output	Load Voltage	V_L	400	V(AC peak or DC)	
	Load Current	I_L	0.15	A	
	Peak Load Current	I_{Peak}	0.45	A	100ms(1 pulse)
	Output Power Dissipation	Pout	750	mW	
Total Power Dissipation		P_T	800	mW	
I/O Breakdown Voltage		$V_{I/O}$	5000	Vrms	RH=60%, 1min
Operating Temperature		T_{opr}	-40 to 85	℃	
Storage Temperature		T_{stg}	-40 to 100	℃	
Pin Soldering Temperature		T_{sol}	260	℃	10 sec max.

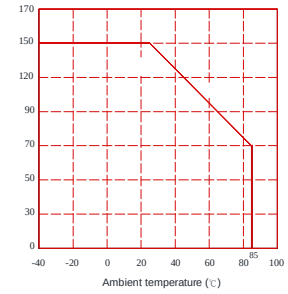
Electrical Characteristics (Ta = 25°C)

Item		Symbol	MIN.	TYP.	MAX.	Units	Conditions
Input	LED Forward Voltage	V_F	1.23	1.3	1.5	V	I_F=10mA
	Operation LED Current	I_{Fon}		0.9	3.0	mA	
	Recovery LED Current	I_{Foff}		0.35	0.5	mA	
	Recovery LED Voltage	V_{Foff}	0.5	1.2		V	
Output	On-Resistance	R_{on}		14	18	Ω	I_F=5mA,I_L=100mA, Time to flow is within 1 sec.
	Off-State Leakage Current	I_{Leak}	0.01	0.02	0.1	uA	V_L=Rating
	Output Capacitance	C_{out}		58		pF	V_L=0, f=1MHz
Transmission	Turn-On Time	T_{on}		0.3	1.0	ms	I_F=5mA, I_L=100mA,
	Turn-Off Time	T_{off}		0.03	0.5	ms	
Coupled	I/O Isolation Resistance	$R_{I/O}$	10^{10}			Ω	DC500V
	I/O Capacitance	$C_{I/O}$		0.8	1.5	pF	f=1MHz

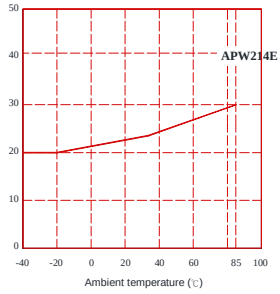
Please obey the following conditions to ensure proper device operation and resetting. Input LED current (Recommended value): IF ≥5mA and ≤30mA

Engineering Data

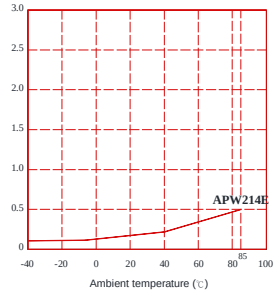
Load current Vs.
Ambient temperature



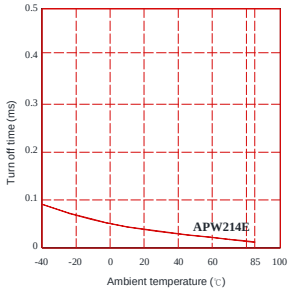
On resistance Vs.
Ambient temperature



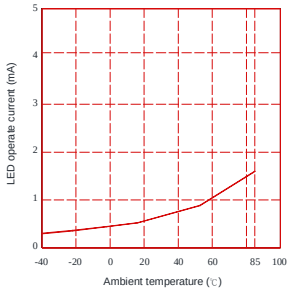
Turn on time Vs.
Ambient temperature



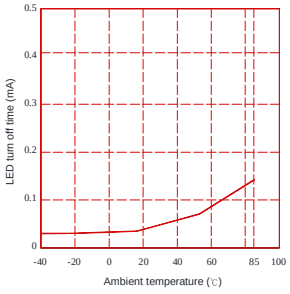
Turn off time Vs.
Ambient temperature



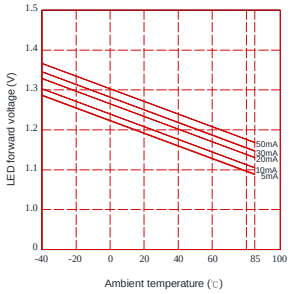
LED operate current Vs.
Ambient temperature



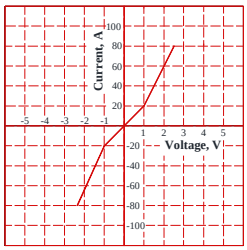
LED turn off current Vs.
Ambient temperature



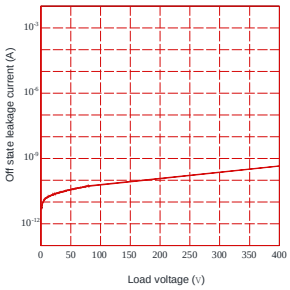
LED forward voltage Vs.
Ambient temperature



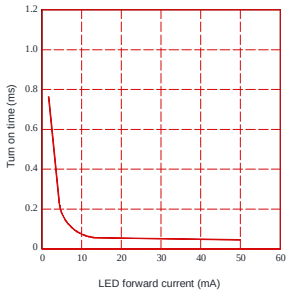
Voltage Vs. currennt characteristics
of output at MOS portion



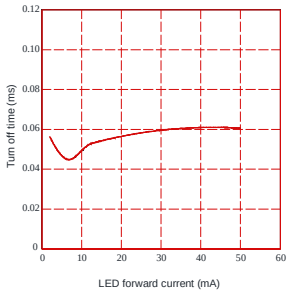
Off state leakage current Vs.
Load voltage characteristics



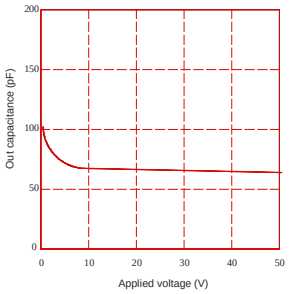
LED foward current Vs.
turn on time characteristics



LED foward current Vs.
turn off time characteristics



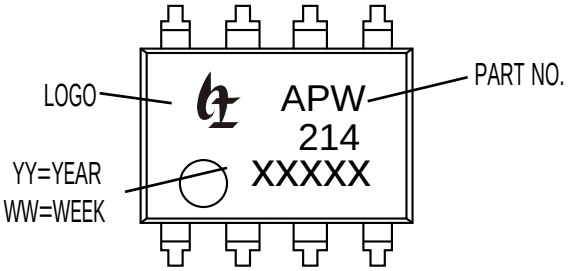
Applied voltage Vs.
output capacitance characteristics



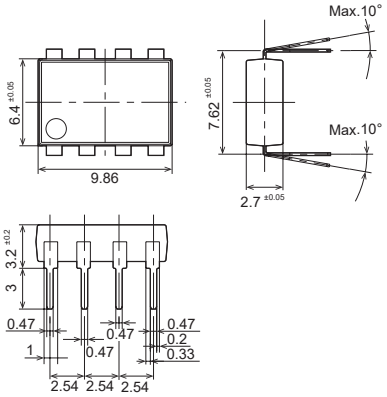
Dimensions and DIP-8 Package

Unit: mm

Marking

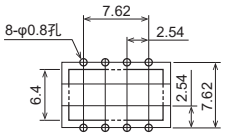


Through hole terminal type



Lable

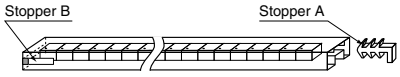
PC board pattern (Bottom view)



DIP Tape dimensions

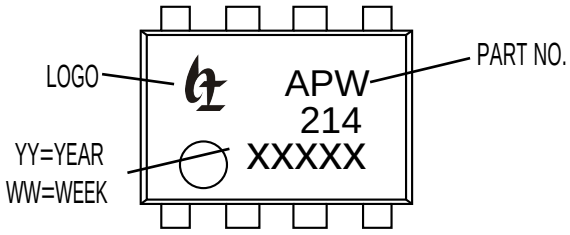
Unit : mm

Devices are packaged in a tube so that pin No. 1 is on the stopper B side. Observe correct orientation when mounting them on PC boards.

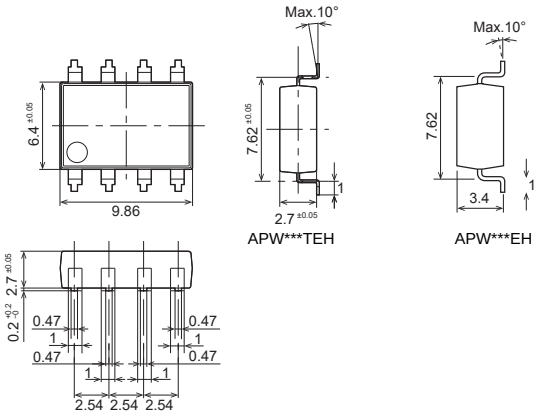


Dimensions and SMD-8 Package Unit: mm

Marking



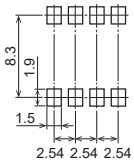
Surface mount terminal type



Lable

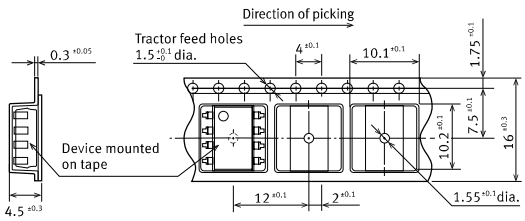
Recommended mounting pad

(Top view)

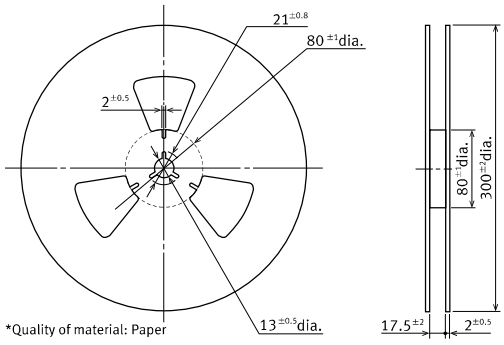


Tape dimensions (tape reel)

Tape dimensions (Unit: mm)

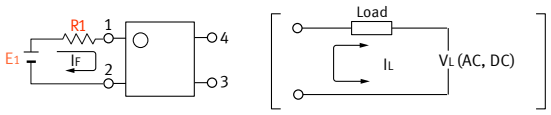


Dimensions of paper tape reel (Unit: mm)



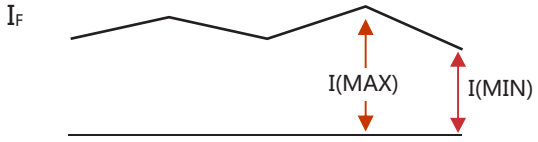
Using Methods

Examples of resistance value to control LED forward current (I_F=5mA)



E1	R1 (Approx)
3.3V	300 Ω
5.0V	600 Ω
12V	1.9KΩ
24V	4.1KΩ

LED forward current must be more than 5mA , at I(MIN) ,and less than 30mA , at I(MAX).



Recommended Operating Conditions

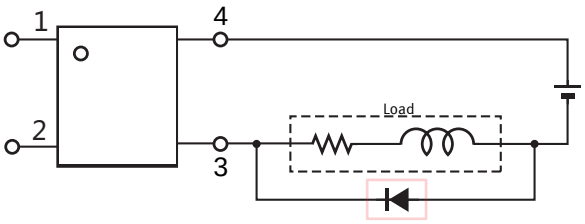
Please obey the following conditions to ensure proper device operation and resetting. Input LED current (Recommended value):

Characteristic	Symbol	Min	Typ.	Max	Unit
Forward current	I_F	5.0	7.0	30	mA

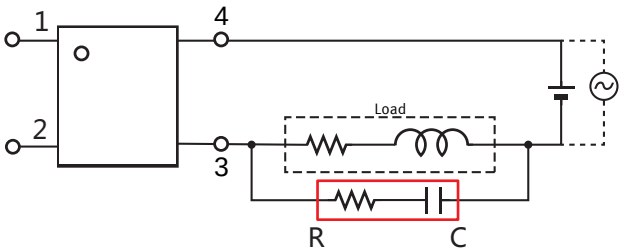
Protection Circuit

Output spike voltages:if an inductive load generates spike voltages which exceed heabsolute maximum rating, the spike voltage shall be limited.

Clamp diode is connected in parallel with the load.
Absorb capacity with external diode.



CR Snubber is connected in parallel with the load.
Absorb capacity with buffer capacity.



When adding diodes, buffer circuits (C-R), and other protections, they need to be installed near the MOS RELAY to be effective.
Adding protection elements may result in a slow reset time, so adjust them according to the actual situation before use.

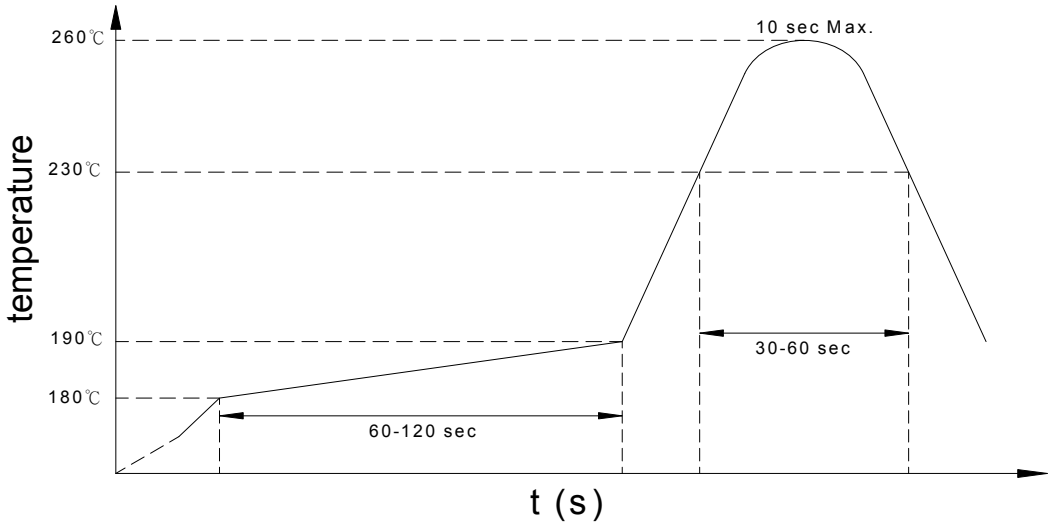
Note: When developing designs using this product, perform the expected performance of the equipment under the operating conditions recommended by the guidelines in this document. Continuous use under heavy loads (including, but not limited to, the application of high temperatures/current/voltage and significant changes in temperature, etc.) may result in deterioration of the reliability of this product.

Recommended Soldering Conditions

(a) Infrared reflow soldering：

- Peak reflow soldering： 260℃ or below (package surface temperature)
- Time of peak reflow temperature： 10 sec
- Time of temperature higher than 230℃： 30-60 sec
- Time to preheat temperature from 180~190℃： 60-120 sec
- Time(s) of reflow： Two
- Flux： Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



(b) Wave soldering：

- Temperature： 260℃ or below (molten solder temperature)
- Time： 10 seconds or less
- Preheating conditions： 120℃ or below (package surface temperature)
- Time(s) of reflow： One
- Flux： Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(c) Cautions：

- Fluxes： Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.
- Avoid shorting between portion of frame and leads.

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- Please be aware of environmental issues and use products in compliance with all applicable laws and regulations governing the inclusion or use of controlled substances, including but not limited to the EU RoHS Directive. APSEMI assumes no responsibility for damages or losses resulting from non-compliance with applicable laws and regulations.

Revision History

Revision	Subjects (major changes since last revision)	Date
1.0	Initial release.	2016.12
1.1	Added a set of backup wafer solutions	2024.05
1.2	Updated: Package information	2025.01

Disclaimer

1. Operating conditions may differ from simulation assumptions in several aspects like level of DC-link voltage, applied gate-voltage and gate-resistor, case and junction temperatures as well as the power circuit stray-inductance. Therefore, deviations of parameters and assumptions used for the simulation and the real application may exist.
2. For these reasons we cannot take any responsibility or liability for the exactness or validity of the form's results. The form cannot replace a detailed reflection of the customers application with all of its operating conditions.
3. Accurate results depend on huge data, so with the measured data is increasing, we should be updated in real time and send it to the corresponding engineer so that he can know it in real time.